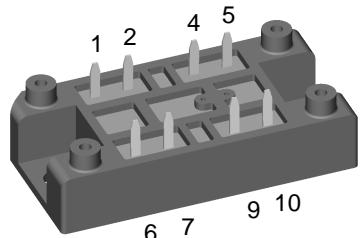
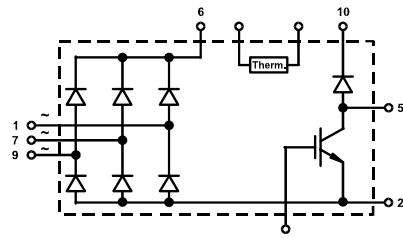


Three Phase Rectifier Bridge with IGBT and Fast Recovery Diode for Braking System

$$\begin{aligned} V_{RRM} &= 1200-1600 \text{ V} \\ I_{dAVM} &= 70 \text{ A} \end{aligned}$$

V _{RRM}	Type
V	
1200	VUB 71-12 NO1
1600	VUB 71-16 NO1



Symbol	Test Conditions		Maximum Ratings	
V_{RRM} I_{dAV} I_{dAVM}	$T_H = 110^\circ\text{C}$, sinusoidal 120° limited by leads		1200 / 1600 59 70	V A A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$, $t = 10 \text{ ms}$, $V_R = 0 \text{ V}$ $T_{VJ} = 150^\circ\text{C}$, $t = 10 \text{ ms}$, $V_R = 0 \text{ V}$		530 475	A A
I^2t	$T_{VJ} = 45^\circ\text{C}$, $t = 10 \text{ ms}$, $V_R = 0 \text{ V}$ $T_{VJ} = 150^\circ\text{C}$, $t = 10 \text{ ms}$, $V_R = 0 \text{ V}$		1400 1130	A A
P_{tot}	$T_H = 25^\circ\text{C}$ per diode		90	W
V_{CES} V_{GE}	$T_{VJ} = 25^\circ\text{C}$ to 150°C Continuous		1200 ± 20	V V
I_{C25}	$T_H = 25^\circ\text{C}$, DC		43	A
I_{C80}	$T_H = 80^\circ\text{C}$, DC		29	A
I_{CM}	t_p = Pulse width limited by T_{VJM}		90	A
P_{tot}	$T_H = 80^\circ\text{C}$		160	W
V_{RRM} I_{FAV} I_{FRMS} I_{FRM}	$T_H = 80^\circ\text{C}$, rectangular $d = 0.5$ $T_H = 80^\circ\text{C}$, rectangular $d = 0.5$ $T_H = 80^\circ\text{C}$, $t_p = 10 \mu\text{s}$, $f = 5 \text{ kHz}$		1200 9 14 90	V A A A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$, $t = 10 \text{ ms}$ $T_{VJ} = 150^\circ\text{C}$, $t = 10 \text{ ms}$		75 60	A A
P_{tot}	$T_H = 25^\circ\text{C}$		40	W
T_{VJ} T_{VJM} T_{stg}			-40...+150 150 -40...+125	°C °C °C
V_{ISOL}	50/60 Hz $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$ $t = 1 \text{ s}$	3000 3600	V~ V~
M_d	Mounting torque	(M5) (10-32 unf)	2-2.5 18-22	Nm lb.in.
Weight	typ.		35	g

Features

- Soldering connections for PCB mounting
 - Isolation voltage 3600 V~
 - Ultrafast freewheeling diode
 - Convenient package outline
 - UL registered E 72873
 - Thermistor

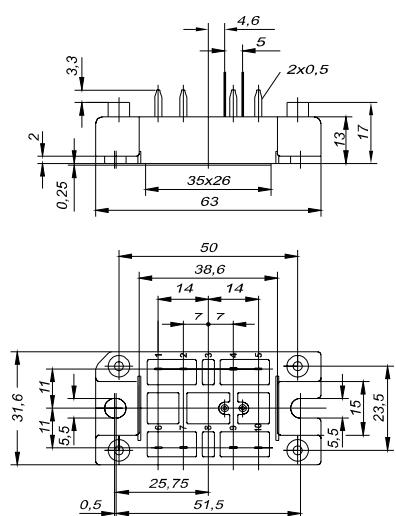
Applications

- Drive Inverters with brake system

Advantages

- 2 functions in one package
 - No external isolation necessary
 - Easy to mount with two screws
 - Suitable for wave soldering
 - High temperature and power cycling capability

Dimensions in mm (1 mm = 0.0394")



Symbol	Test Conditions	Characteristic Values			
		($T_{VJ} = 25^\circ C$, unless otherwise specified)	min.	typ.	max.
I_R	$V_R = V_{RRM}$, $T_{VJ} = 25^\circ C$ $V_R = V_{RRM}$, $T_{VJ} = 150^\circ C$		0.1	mA	
V_F	$I_F = 25 A$, $T_{VJ} = 25^\circ C$		1.3	V	
V_{TO} r_T	For power-loss calculations only $T_{VJ} = 150^\circ C$		0.85	V	
R_{thJH}	per diode		8.5	mΩ	
$V_{BR(CES)}$ $V_{GE(th)}$	$V_{GS} = 0 V$, $I_C = 3 mA$ $I_C = 10 mA$	1200 5	8	V	
I_{GES}	$V_{GE} = \pm 20 V$		500	nA	
I_{CES}	$T_{VJ} = 25^\circ C$, $V_{CE} = V_{CES}$ $T_{VJ} = 125^\circ C$, $V_{CE} = 0.8 V_{CES}$		700	μA	
V_{CEsat}	$V_{GE} = 15 V$, $I_C = 25 A$		1.5	mA	
t_{sc} (SCSOA)	$V_{GE} = 15 V$, $V_{CE} = 600 V$, $T_{VJ} = 125^\circ C$, $R_G = 22 \Omega$, non repetitive		10	μs	
RBSOA	$V_{GE} = 15 V$, $V_{CE} = 800 V$, $T_{VJ} = 125^\circ C$, $R_G = 22 \Omega$, Clamped Inductive load, $L = 100 \mu H$		50	A	
C_{ies}	$V_{CE} = 25 V$, $f = 1 MHz$, $V_{GE} = 0 V$	4.5		nF	
$t_{d(on)}$ $t_{d(off)}$ t_{fi} E_{on} E_{off}	$\left. \begin{array}{l} V_{CE} = 600 V, I_C = 25 A \\ V_{GE} = 15 V, R_G = 22 \Omega \\ \text{Inductive load: } L = 100 \mu H \\ T_{VJ} = 125^\circ C \end{array} \right\}$	300 350 1600 6 8	ns ns ns mJ mJ		
R_{thJH}			0.8	K/W	
I_R	$V_R = V_{RRM}$, $T_{VJ} = 25^\circ C$ $V_R = 800 V$, $T_{VJ} = 150^\circ C$	4	0.2 6	mA	
V_F	$I_F = 12 A$, $T_{VJ} = 25^\circ C$		2.7	V	
V_{TO} r_T	For power-loss calculations only $T_{VJ} = 150^\circ C$		1.65	V	
I_{RM}	$I_F = 25 A$, $-di_F/dt = 100 A/\mu s$ $V_R = 100 V$	6.5	7	A	
t_{rr}	$I_F = 1 A$, $-di_F/dt = 100 A/\mu s$ $V_R = 30 V$	50	70	ns	
R_{thJH}			3.12	K/W	
R_{25}	Siemens Typ S 891/2,2k/+9		2,2	kΩ	
d_s d_A a	Creep distance on surface Strike distance in air Maximum allowable acceleration		12.7 9.4 50	mm mm m/s ²	